

General Description:

HM1N60PR, the silicon N-channel Enhanced VDMOSFETs, is obtained by the self-aligned planar Technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. The transistor can be used in various power switching circuit for system miniaturization and higher efficiency. The package form is SOT-89-3L, which accords with the RoHS standard.

Features:

- **Fast Switching**
- **Low ON Resistance**($R_{ds(on)} \leq 10.5 \Omega$)
- **Low Gate Charge** (Typical Data: 6.0nC)
- **Low Reverse transfer capacitances**(Typical: 4pF)
- **100% Single Pulse avalanche energy Test**

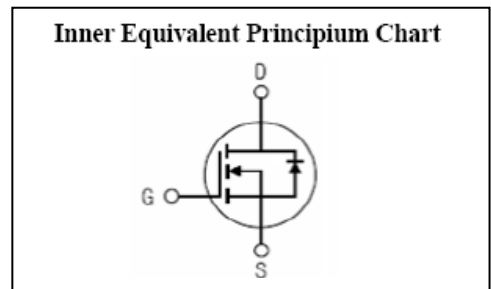
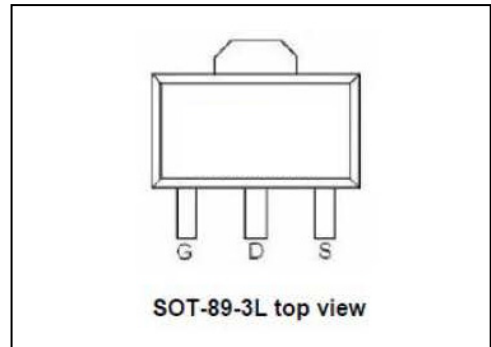
Applications:

Power switch circuit of adaptor and charger.

Absolute ($T_c = 25^\circ\text{C}$ unless otherwise specified):

Symbol	Parameter	Rating	Units
V_{DSS}	Drain-to-Source Voltage	600	V
I_D	Continuous Drain Current	1.0	A
	Continuous Drain Current $T_c = 100^\circ\text{C}$	0.7	A
I_{DM}^{a1}	Pulsed Drain Current	4.0	A
V_{GS}	Gate-to-Source Voltage	± 30	V
E_{AS}^{a2}	Single Pulse Avalanche Energy	70	mJ
E_{AR}^{a1}	Avalanche Energy ,Repetitive	6	mJ
I_{AR}^{a1}	Avalanche Current	1.1	A
dv/dt^{a3}	Peak Diode Recovery dv/dt	5.0	V/ns
P_D	Power Dissipation	3	W
	Derating Factor above 25°C	0.024	W/ $^\circ\text{C}$
T_J, T_{stg}	Operating Junction and Storage Temperature Range	150, -55 to 150	$^\circ\text{C}$
T_L	Maximum Temperature for Soldering	300	$^\circ\text{C}$

V_{DSS}	600	V
I_D	1.0	A
$P_D (T_c=25^\circ\text{C})$	3	W
$R_{DS(ON)Typ}$	9	Ω



Electrical Characteristics (Tc= 25℃ unless otherwise specified):

OFF Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
V _{DSS}	Drain to Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	600	--	--	V
Δ BV _{DSS} / Δ T _J	Bvdss Temperature Coefficient	ID=250uA, Reference 25℃	--	0.71	--	V/℃
I _{DSS}	Drain to Source Leakage Current	V _{DS} = 600V, V _{GS} = 0V, T _a = 25℃	--	--	25	μA
		V _{DS} =480V, V _{GS} = 0V, T _a = 125℃	--	--	250	
I _{GSS(F)}	Gate to Source Forward Leakage	V _{GS} =+30V	--	--	100	nA
I _{GSS(R)}	Gate to Source Reverse Leakage	V _{GS} =-30V	--	--	-100	nA

ON Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
R _{DS(ON)}	Drain-to-Source On-Resistance	V _{GS} =10V, I _D =0.5A	--	9	10.5	Ω
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	2.0		4.0	V
Pulse width tp ≤ 380μs, δ ≤ 2%						

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
g _{fs}	Forward Transconductance	V _{DS} =15V, I _D =0.5A	--	0.70	--	S
C _{iss}	Input Capacitance	V _{GS} = 0V V _{DS} = 25V f = 1.0MHz	--	150	--	pF
C _{oss}	Output Capacitance		--	25	--	
C _{rss}	Reverse Transfer Capacitance		--	4	--	

Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
t _{d(ON)}	Turn-on Delay Time	I _D =1.0A V _{DD} = 300V V _{GS} = 10V R _G = 25Ω	--	23	--	ns
t _r	Rise Time		--	27	--	
t _{d(OFF)}	Turn-Off Delay Time		--	12	--	
t _f	Fall Time		--	27	--	
Q _g	Total Gate Charge	I _D =1.0A V _{DD} =480V V _{GS} = 10V	--	6.0		nC
Q _{gs}	Gate to Source Charge		--	1.1		
Q _{gd}	Gate to Drain (“Miller”)Charge		--	3.5		

Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
I _S	Continuous Source Current (Body Diode)		--	--	1.0	A
I _{SM}	Maximum Pulsed Current (Body Diode)		--	--	4.0	A
V _{SD}	Diode Forward Voltage	I _S =1.0A, V _{GS} =0V	--	--	1.5	V
trr	Reverse Recovery Time	I _S =1.0A, T _j = 25° C dI _F /dt=100A/us, V _{GS} =0V	--	140		ns
Qrr	Reverse Recovery Charge		--	224		nC
I _{RRM}	Reverse Recovery Current		--	3.2		A
Pulse width tp≤380μs, δ ≤2%						

Symbol	Parameter	Typ.	Units
$R_{\theta JC}$	Junction-to-Case	41.7	$^\circ C/W$
$R_{\theta JA}$	Junction-to-Ambient	200	$^\circ C/W$

^{a1}: Repetitive rating; pulse width limited by maximum junction temperature

^{a2}: $L=10.0mH, I_D=3.7A, \text{Start } T_J=25^\circ C$

^{a3}: $I_{SD}=1.2A, di/dt \leq 100A/us, V_{DD} \leq BV_{DS}, \text{Start } T_J=25^\circ C$

Characteristics Curve:

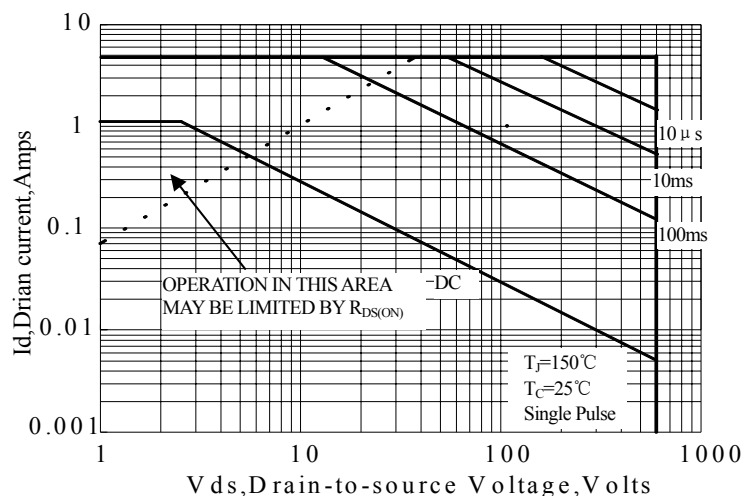


Figure 1 Maximum Forward Bias Safe Operating Area

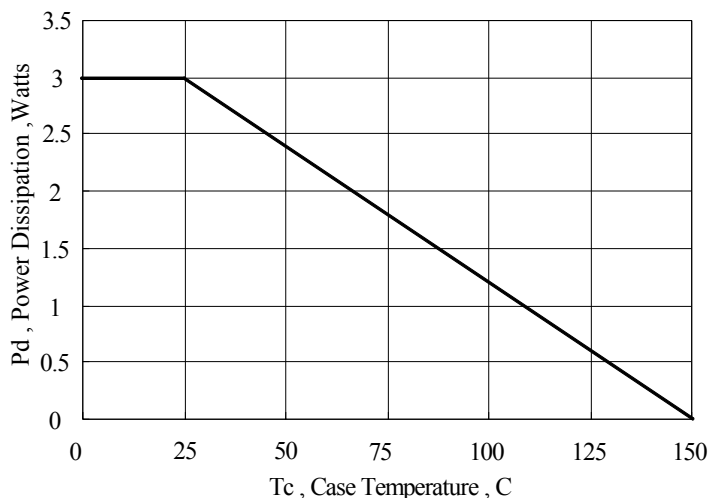


Figure 2 Maximum Power Dissipation vs Case Temperature

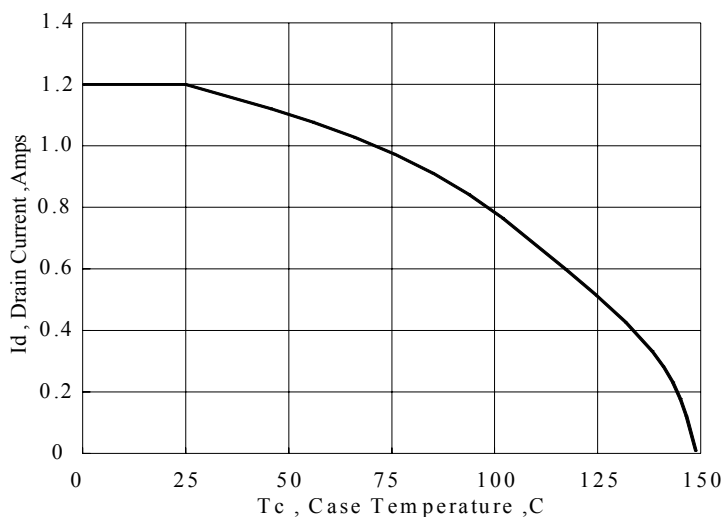


Figure 3 Maximum Continuous Drain Current vs Case Temperature

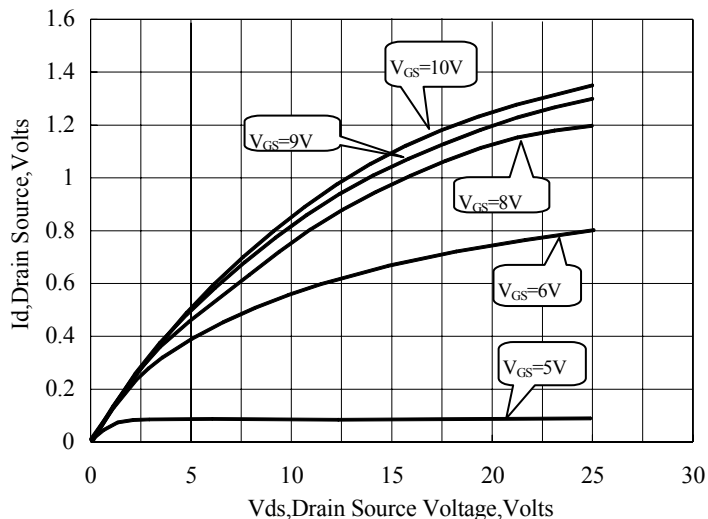


Figure 4 Typical Output Characteristics

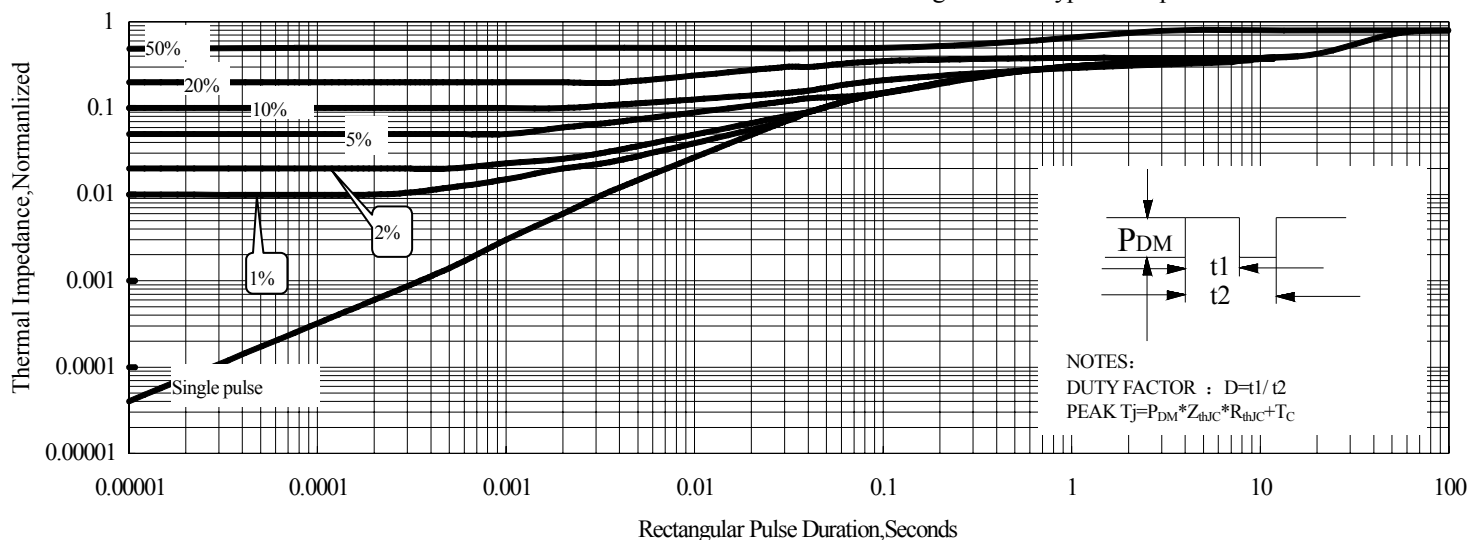
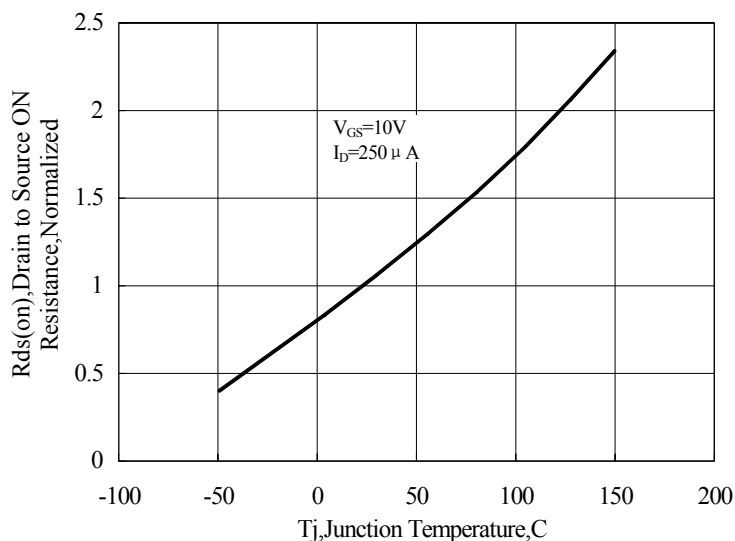
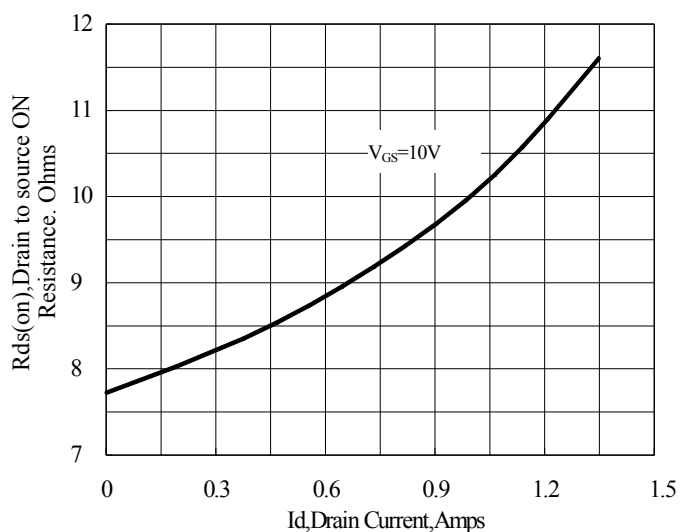
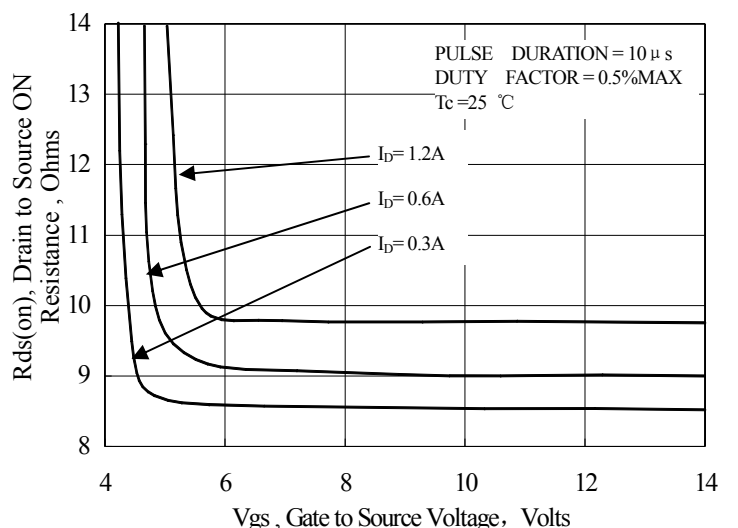
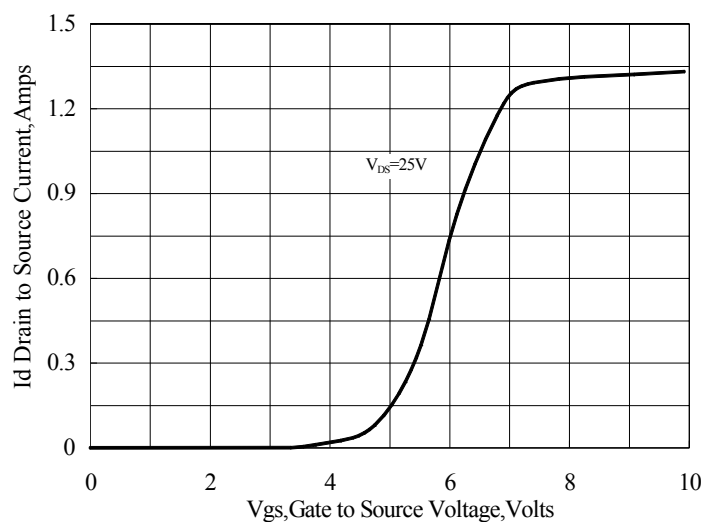
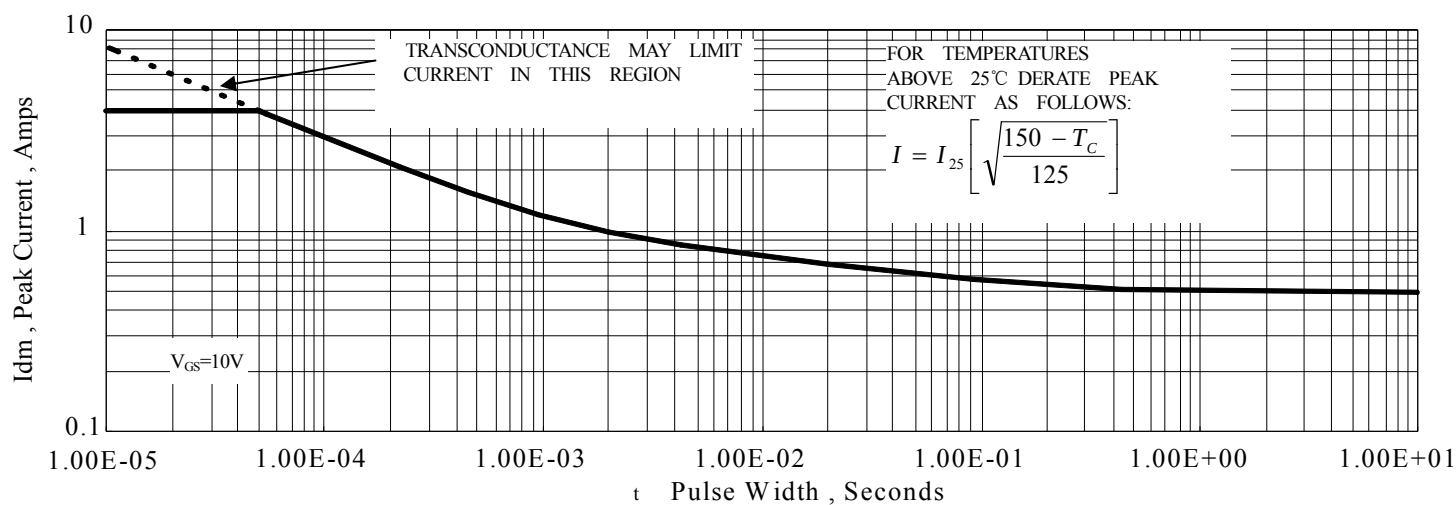


Figure 5 Maximum Effective Thermal Impedance, Junction to Case



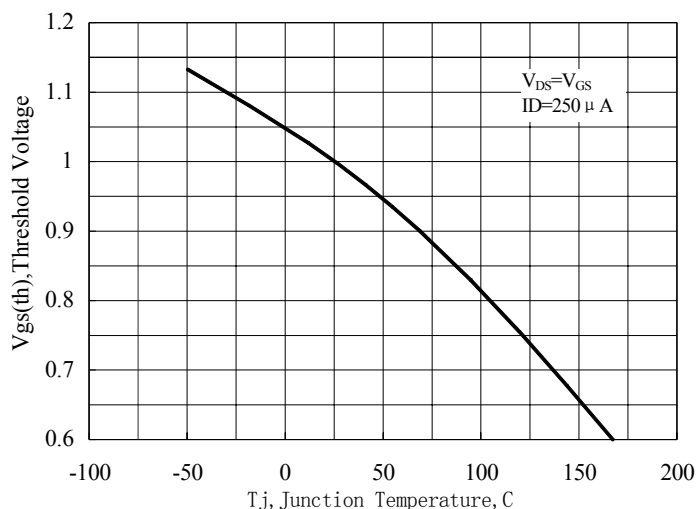


Figure 11 Typical Theshold Voltage vs Junction Temperature

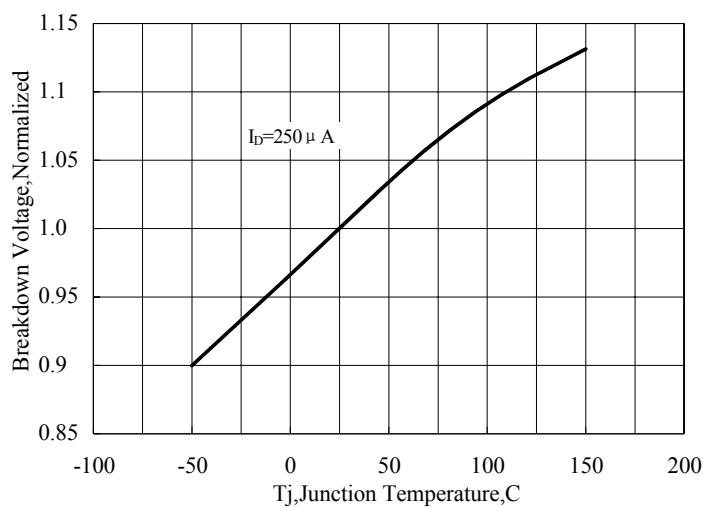


Figure 12 Typical Breakdown Voltage vs Junction Temperature

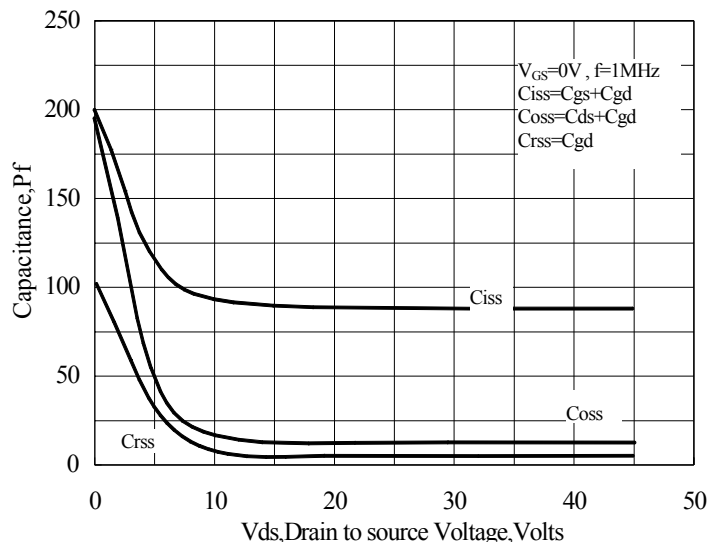


Figure 13 Typical Capacitance vs Drain to Source Voltage

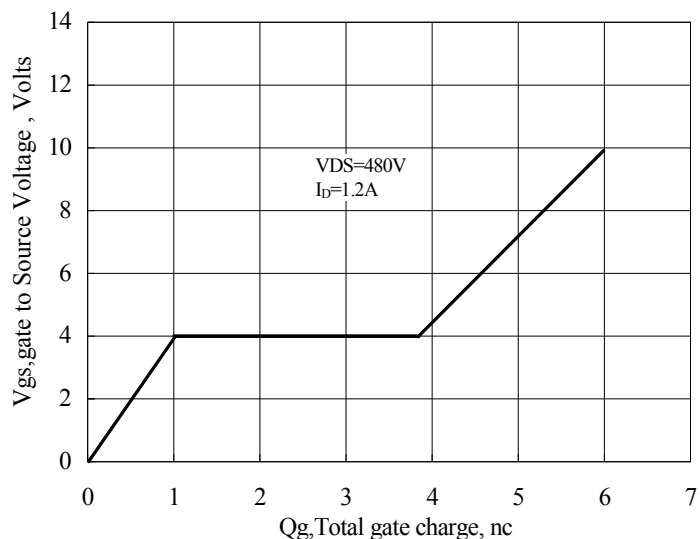


Figure 14 Typical Gate Charge vs Gate to Source Voltage

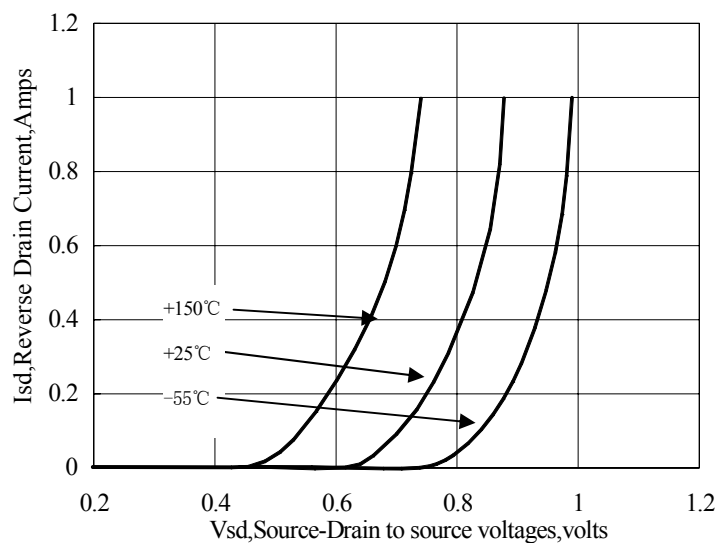


Figure 15 Typical Body Diode Transfer Characteristics

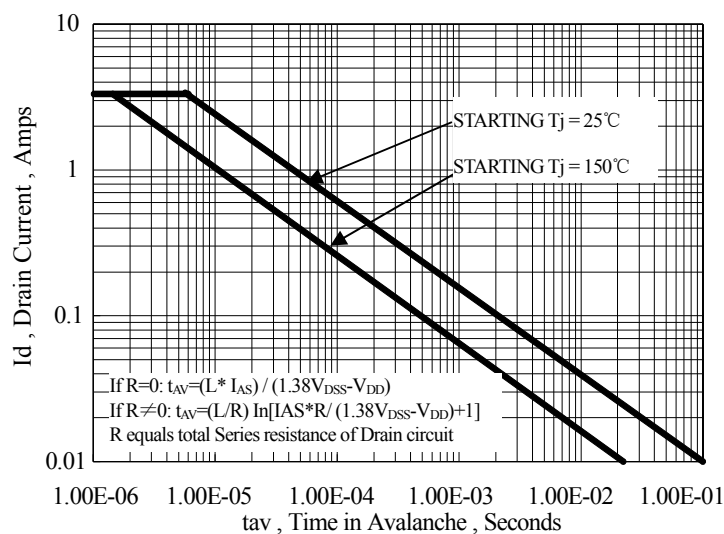
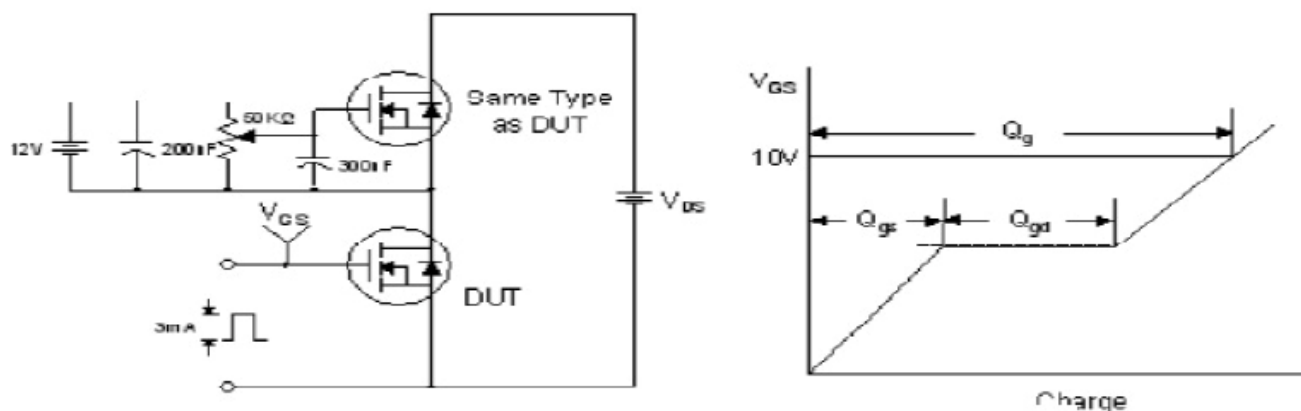
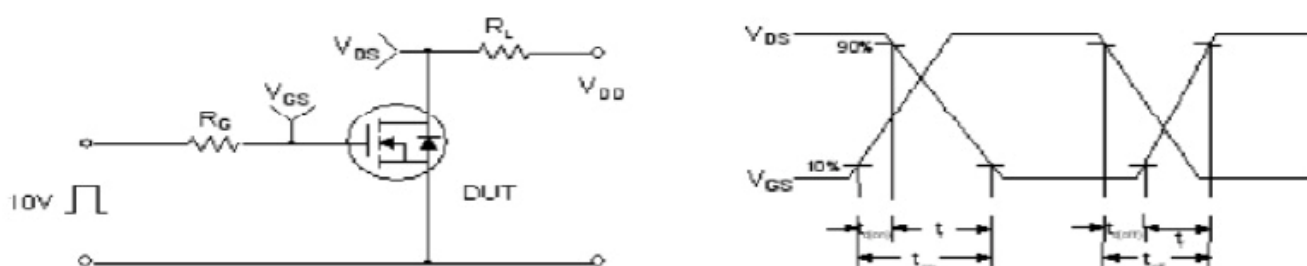


Figure 16 Unclamped Inductive Switching Capability

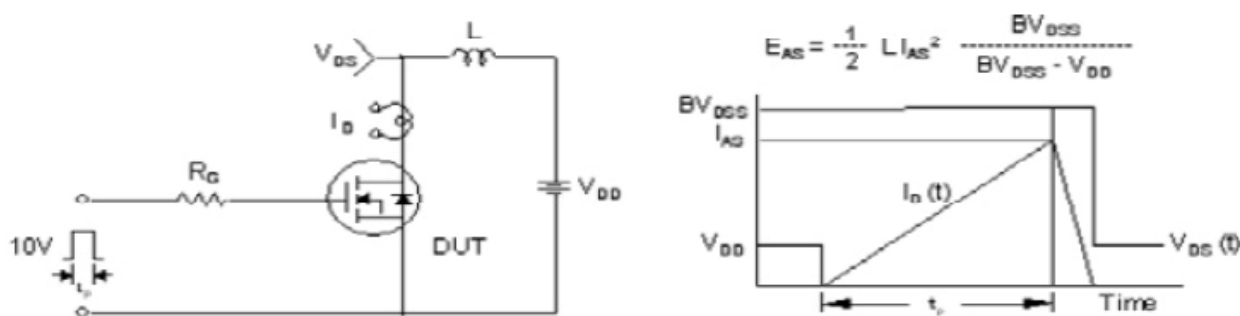
Test Circuit and Waveform



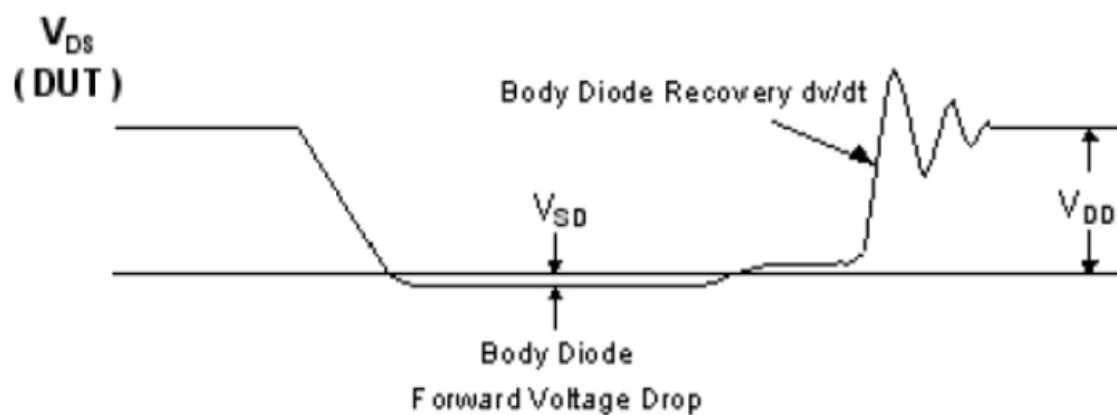
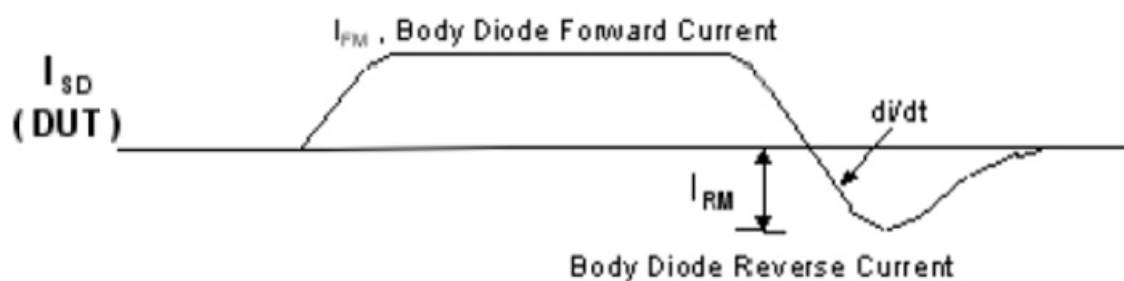
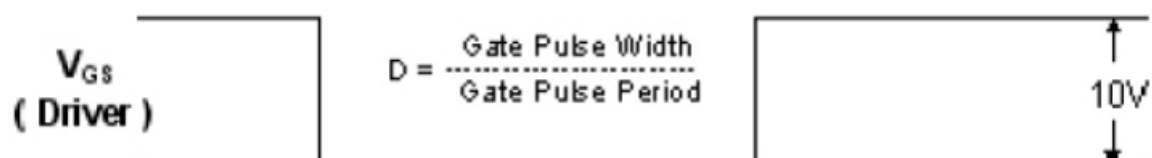
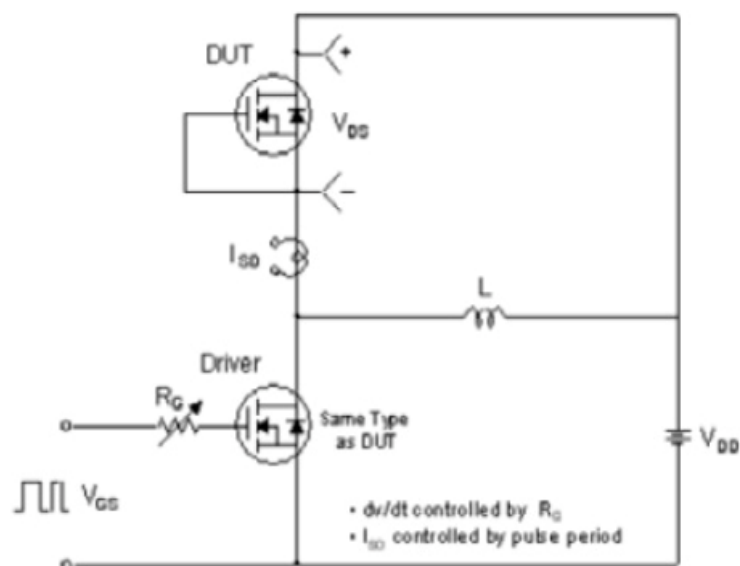
Gate Charge Test Circuit and Waveform



Resistive Switching Test Circuit and Waveform

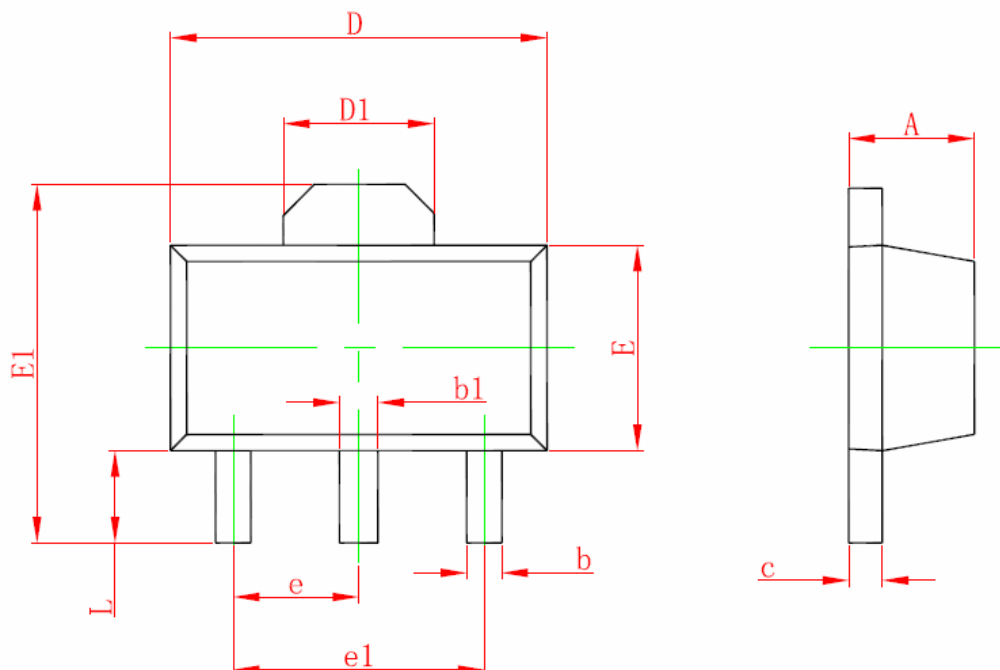


Unclamped Inductive Switching Test Circuit and Waveform



Diode Reverse Recovery Test Circuit and Waveform

SOT-89-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF.		0.061 REF.	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP.		0.060 TYP.	
e1	3.000 TYP.		0.118 TYP.	
L	0.900	1.200	0.035	0.047

Notes

1. All dimensions are in millimeters.
2. Tolerance $\pm 0.10\text{mm}$ (4 mil) unless otherwise specified
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

The name and content of poisonous and harmful material in products

Part's Name	Hazardous Substance					
	Pb	Hg	Cd	Cr(VI)	PBB	PBDE
Limit	≤0.1%	≤0.1%	≤0.01%	≤0.1%	≤0.1%	≤0.1%
Lead Frame	○	○	○	○	○	○
Molding Compound	○	○	○	○	○	○
Chip	○	○	○	○	○	○
Wire Bonding	○	○	○	○	○	○
Solder	×	○	○	○	○	○
Note	○: means the hazardous material is under the criterion of SJ/T11363-2006. ×: means the hazardous material exceeds the criterion of SJ/T11363-2006.					

Warnings

1. Exceeding the maximum ratings of the device in performance may cause damage to the device, even the permanent failure, which may affect the dependability of the machine. It is suggested to be used under 80 percent of the maximum ratings of the device.
2. When installing the heatsink, please pay attention to the torsional moment and the smoothness of the heatsink.
3. VDMOSFETs is the device which is sensitive to the static electricity, it is necessary to protect the device from being damaged by the static electricity when using it.
4. This publication is made by H&M Semiconductor and subject to regular change without notice.